ELECTRONICS, INC.
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NTE2698
Silicon NPN Transistor
General Purpose
TO3PN Type Package

Features:
- Low Collector Saturation Voltage: $V_{CE(sat)}$ = 0.5V Max @ I_C = 3A
- Collector–Emitter Breakdown Voltage: $V_{(BR)CEO}$ = 120V Min
- Good Linearity of h_{FE}

Applications:
- Humidifier
- DC/DC Converter
- General Purpose Power Amplifiers

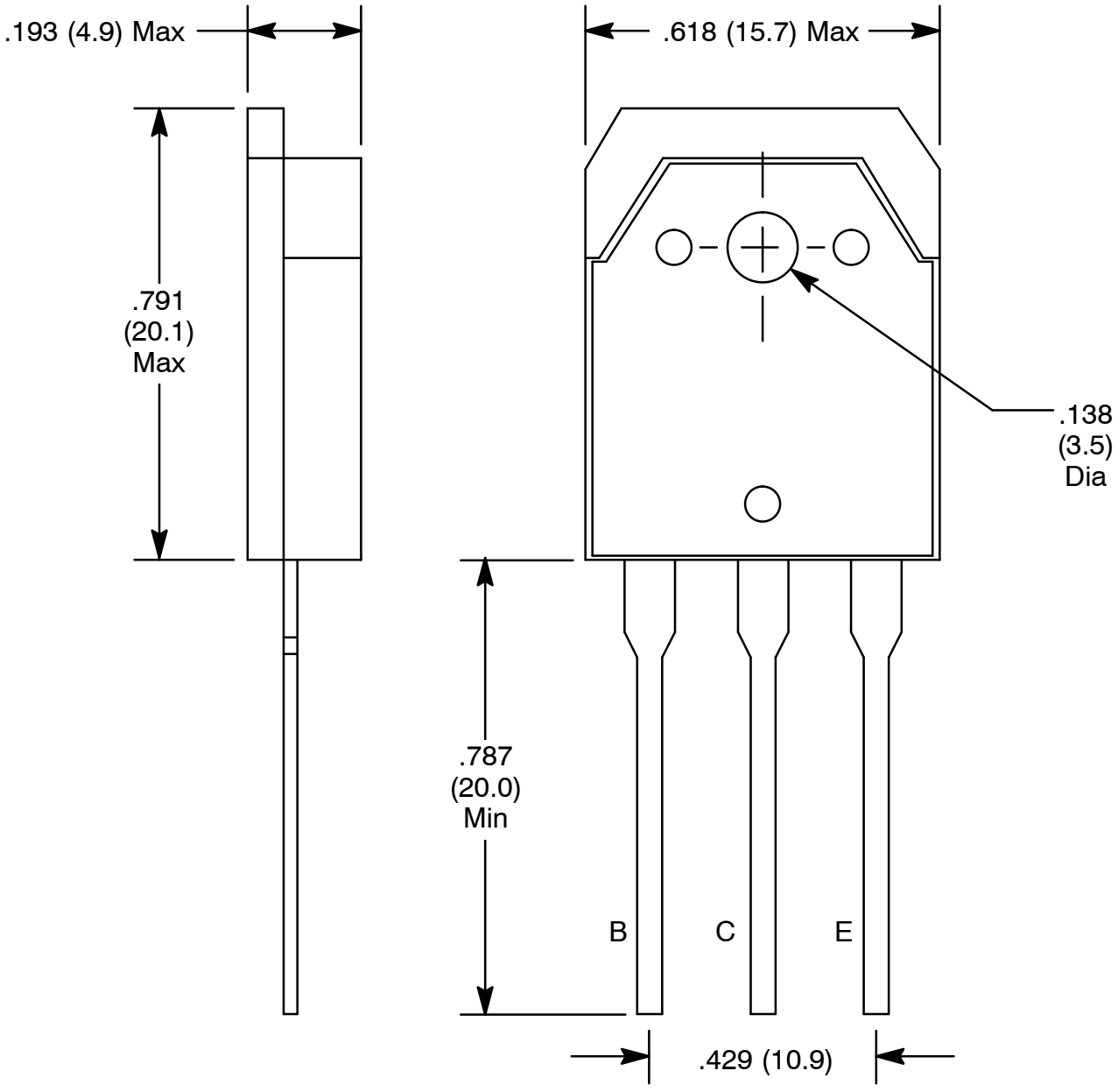
Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 200V
Collector–Emitter Voltage, V_{CEO} 120V
Emitter–Base Voltage, V_{EBO} 8V
Collector Current, I_C
  Continuous 7A
  Pulse 14A
Continuous Base Current, I_B 3A
Collector Power Dissipation (T_C = +25°C), P_C 70W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_C = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 50mA, I_B = 0	120	–	–	V
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 3A, I_B = 300mA	–	–	0.5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 3A, I_B = 300mA	–	–	1.2	V
Collector Cut–Off Current	I_{CBO}	V_{CB} = 200V, I_E = 0	–	–	100	μA
Emitter Cut–Off Current	I_{EBO}	V_{EB} = 8V, I_C = 0	–	–	100	μA
DC Current Gain	h_{FE}	I_C = 3A, V_{CE} = 4V	100	–	200	

RoHS


.193 (4.9) Max
.618 (15.7) Max
.791
(20.1)
Max
.138
(3.5)
Dia
.787
(20.0)
Min
B
C
E
.429 (10.9)